

## CLAIMS

[1] A susceptor that is used in semiconductor epitaxial growth, comprising:

a barrel type susceptor having a plurality of surfaces on an outer side of each of which a plurality of substrates is freely disposed; and a member that has the barrel type susceptor disposed inside thereof and surfaces each of which is oppositely disposed tilting in the same direction as each of the surfaces of the barrel type susceptor.

[2] A susceptor that is used in semiconductor epitaxial growth, comprising:

a barrel type susceptor having a plurality of surfaces on an inner side of each of which a plurality of substrates is freely disposed; and a member that has the barrel type susceptor disposed at the peripheral portion thereof and surfaces each of which is oppositely disposed tilting in the same direction as each of the surfaces of the barrel type susceptor.

[3] The susceptor according to claim 1 or 2, wherein each of surfaces on a side of the barrel type susceptor of the member allows placing a plurality of substrates.

[4] The susceptor according to claim 1 or 2, wherein either one or both of the barrel type susceptor and the member are a heater.

[5] The susceptor according to claim 1 or 2, wherein the

susceptor is made of a base material containing graphite.

[6] The susceptor according to claim 5, wherein the susceptor is covered with polycrystalline silicon carbide or polycrystalline tantalum carbide.